

Amendments to the Claims

This listing of claims replaces all prior versions and listings of claims in the application.

Listing of Claims

1. (Currently Amended) A light-emitting device comprising:
a pixel comprising:
a light-emitting element,
a first transistor for determining a value of a current flowing to the light-emitting element, and
a second transistor for determining a light emission or non light emission of the light-emitting element depending on a video signal input ~~to~~ through a signal line,
wherein the light-emitting element, the first transistor, and the second transistor are connected in series between a first power line and a counter electrode of the light-emitting element,
wherein a gate electrode of the first transistor is connected to a second power line,
wherein the signal line, the first power line, and the second power line are provided in parallel with each other, ~~and~~
wherein the first power line is provided between the signal line and the second power line, and
wherein the second power line has an electric potential so that the first transistor operates in a saturation region when the second transistor is in an on-state.

2. (Currently Amended) A light-emitting device comprising:
a pixel comprising:
a light-emitting element,
a first transistor for determining a value of a current flowing to the light-emitting element,

a second transistor for determining a light emission or non light emission of the light-emitting element depending on a video signal input ~~to~~through a signal line, and

a third transistor for controlling an input of the video signal,

wherein the light-emitting element, the first transistor, and the second transistor are connected in series between a first power line and a counter electrode of the light-emitting element,

wherein a gate electrode of the first transistor is connected to a second power line,

wherein the signal line, the first power line, and the second power line are provided in parallel with each other, [[and]]

wherein the first power line is provided between the signal line and the second power line, and

wherein the second power line has an electric potential so that the first transistor operates in a saturation region when the second transistor is in an on-state.

3. (Currently Amended) A light-emitting device comprising:

a pixel comprising:

a light-emitting element,

a first transistor for determining a value of a current flowing to the light-emitting element,

a second transistor for determining a light emission or non light emission of the light-emitting element depending on a video signal input through a signal line,

a third transistor for controlling an input of the video signal, and

a fourth transistor for forcing the light-emitting element into a non-emission state irrelevant from the video signal,

wherein the light-emitting element, the first transistor, and the second transistor are connected in series between a first power line and a counter electrode of the light-emitting element,

wherein a gate electrode of the first transistor is connected to a second power line,

wherein the signal line, the first power line, and the second power line are provided in parallel with each other, [[and]]

wherein the first power line is provided between the signal line and the second power line, and

wherein the second power line has an electric potential so that the first transistor operates in a saturation region when the second transistor is in an on-state.

4. (Previously Presented) The light-emitting device according to claim 1, wherein the first transistor and the second transistor are identical in conductivity.

5. (Previously Presented) The light-emitting device according to claim 1, wherein the first transistor comprises a depletion type.

6. (Previously Presented) The light-emitting device according to claim 1, wherein the first transistor has a channel length longer than a channel width, and the second transistor has a channel length equal to or shorter than a channel width.

7. (Previously Presented) The light-emitting device according to claim 6, wherein a ratio of the channel length to the channel width of the first transistor is 5 or more.

8. (Currently Amended) An element substrate comprising:
a pixel comprising:

a pixel electrode;

a first transistor for determining a value of a current flowing to the pixel electrode, and

a second transistor for determining a supply or non-supply of a current to the pixel electrode depending on a video signal input ~~to~~ through a signal line,

wherein the first transistor and the second transistor are connected in series between a first power line and the pixel electrode,

wherein a gate electrode of the first transistor is connected to a second power line,

wherein the signal line, the first power line, and the second power line are provided in parallel with each other, [[and]]

wherein the first power line is provided between the signal line and the second power line, and

wherein the second power line has an electric potential so that the first transistor operates in a saturation region when the second transistor is in an on-state.

9. (Previously Presented) The element substrate according to claim 8, wherein each of the first transistor and the second transistor has a P-type conductivity, and a threshold value of the first transistor is higher than that of the second transistor.

10. (Previously Presented) The element substrate according to claim 8, wherein each of the first transistor and the second transistor has an N-type conductivity, and a threshold value of the first transistor is lower than that of the second transistor.

11. (Previously Presented) The element substrate according to claim 8, wherein the first transistor comprises a depletion type.

12. (Previously Presented) The element substrate according to claim 8, wherein the first transistor has a channel length longer than a channel width, and the second transistor has a channel length equal to or shorter than a channel width.

13. (Previously Presented) The element substrate according to claim 12, wherein a ratio of the channel length to the channel width of the first transistor is 5 or more.

14. (Previously Presented) The light-emitting device according to claim 2, wherein the first transistor and the second transistor are identical in conductivity.

15. (Previously Presented) The light-emitting device according to claim 3, wherein the first transistor and the second transistor are identical in conductivity.

16. (Previously Presented) The light-emitting device according to claim 2, wherein the first transistor comprises a depletion type.

17. (Previously Presented) The light-emitting device according to claim 3, wherein the first transistor comprises a depletion type.

18. (Previously Presented) The light-emitting device according to claim 2, wherein the first transistor has a channel length longer than a channel width, and the second transistor has a channel length equal to or shorter than a channel width.

19. (Previously Presented) The light-emitting device according to claim 3, wherein the first transistor has a channel length longer than a channel width, and the second transistor has a channel length equal to or shorter than a channel width.

20. (Previously Presented) The element substrate according to claim 9, wherein the first transistor comprises a depletion type.

21. (Previously Presented) The element substrate according to claim 10, wherein the first transistor comprises a depletion type.

22. (Previously Presented) The element substrate according to claim 9, wherein the first transistor has a channel length longer than a channel width, and the second transistor has a channel length equal to or shorter than a channel width.

23. (Previously Presented) The element substrate according to claim 10, wherein the first transistor has a channel length longer than a channel width, and the second transistor has a channel length equal to or shorter than a channel width.

24. (Previously Presented) The light-emitting device according to claim 18, wherein a ratio of the channel length to the channel width of the first transistor is 5 or more.

25. (Previously Presented) The light-emitting device according to claim 19, wherein a ratio of the channel length to the channel width of the first transistor is 5 or more.

26. (Previously Presented) The light-emitting device according to claim 1, wherein the light-emitting device is incorporated into at least one selected from the group consisting of a cellular phone, a mobile computer, a game machine, an electronic book, a video camera, a digital camera, a goggle display, a display device, and a navigation system.

27. (Previously Presented) The light-emitting device according to claim 2, wherein the light-emitting device is incorporated into at least one selected from the group consisting of a cellular phone, a mobile computer, a game machine, an electronic book, a video camera, a digital camera, a goggle display, a display device, and a navigation system.

28. (Previously Presented) The light-emitting device according to claim 3, wherein the light-emitting device is incorporated into at least one selected from the group consisting of a cellular phone, a mobile computer, a game machine, an electronic book, a video camera, a digital camera, a goggle display, a display device, and a navigation system.

29. (Previously Presented) The element substrate according to claim 8, wherein the element substrate is incorporated into at least one selected from the group consisting of a cellular phone, a mobile computer, a game machine, an electronic book, a video camera, a digital camera, a goggle display, a display device, and a navigation system.

30. (Currently Amended) The light-emitting device according to claim 1, wherein a ~~potential of the gate electrode of the first transistor~~ the electric potential of the second power line is fixed.

31. (Currently Amended) The light-emitting device according to claim 2, wherein a ~~potential of the gate electrode of the first transistor~~ the electric potential of the second power line is fixed.

32. (Currently Amended) The light-emitting device according to claim 3, wherein a ~~potential of the gate electrode of the first transistor~~ the electric potential of the second power line is fixed.

33. (Currently Amended) The element substrate according to claim 8, wherein a ~~potential of the gate electrode of the first transistor~~ the electric potential of the second power line is fixed.